

What is claimed is:

1. A field effect transistor in which at least one vertically aligned semiconductor column (2) of a diameter in the nanometer range is present between a source electrode and a drain electrode (1, 7) and is annularly surrounded by a gate electrode with an insulating space between them,  
characterized by the fact that  
the semiconductor columns (2) are embedded in a first and a second insulating layer (3, 5) between which there is provided a metal layer (4) extending to the outside as a gate electrode whose ends penetrating through the second insulating layer (5) are partially converted to an insulator (6) or partially removed and filled by an insulating material.
- 15 2. A method of fabricating a field effect transistor in which at least one vertically aligned semiconductor column (2) of a diameter in the nanometer range is present between a source electrode and a drain electrode (1, 7) and is annularly surrounded by a gate electrode with an insulating space between them,  
characterized by the fact that
  - free-standing semiconductor columns are grown vertically on a conductive substrate;
  - a first insulating layer is deposited on the semiconductor columns;
  - a first conductive metal layer and a second insulating layer are deposited thereon;
  - the developing laminates is etched planar to the point of the portion of the first metal layer covering the semiconductor columns is removed again;
  - the end of the metal layer penetrating to the surface of the laminate are etched back in a metal-specific manner and a third insulating layer is deposited on the laminate with subsequent

renewed planar etching;  
or  
the ends of the metal layer penetrating to the surface of the  
laminate are converted to an insulator by oxidizing or nitriding;  
5 and  
- finally depositing a second metal layer on the laminate.

3. The method of claim 2,  
characterized by the fact that
- 10 the laminate or individual layers are divided into individual arrays by a  
lithographic process.
  
4. The method of claim 2,  
characterized by the fact that
- 15 the growing of the semiconductor columns is carried out electro-chemically.
  
5. The method of claim 2,  
characterized by the fact that  
the growing of the semiconductor columns is carried out by sputtering.
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6. The method of claim 2,  
characterized by the fact that  
the growing of the semiconductor columns is carried out by a CVD process.
  
- 25 7. The method of claim 2,  
characterized by the fact that  
the growing of the semiconductor columns is carried out by vaporization.
  
- 30 8. The method of claim 2,  
characterized by the fact that  
the growing of the semiconductor columns is carried out in ion trace channels  
of a polymeric film which is subsequently removed.